

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

5HN01M — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Ultrahigh-speed switching
- · 4V drive

Specifications

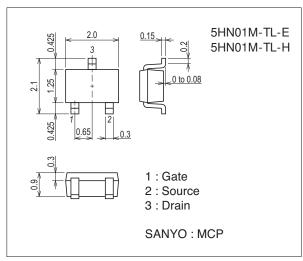
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		50	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		0.1	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	0.4	Α
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Package Dimensions

unit : mm (typ) 7023A-010

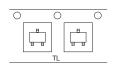


Product & Package Information

• Package : MCP

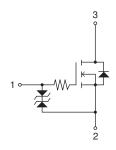
• JEITA, JEDEC : SC-70, SOT-323 • Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL



Marking

Electrical Connection



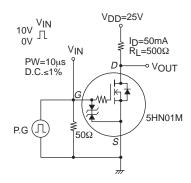
^{*} Machine Model

5HN01M

Electrical Characteristics at Ta=25°C

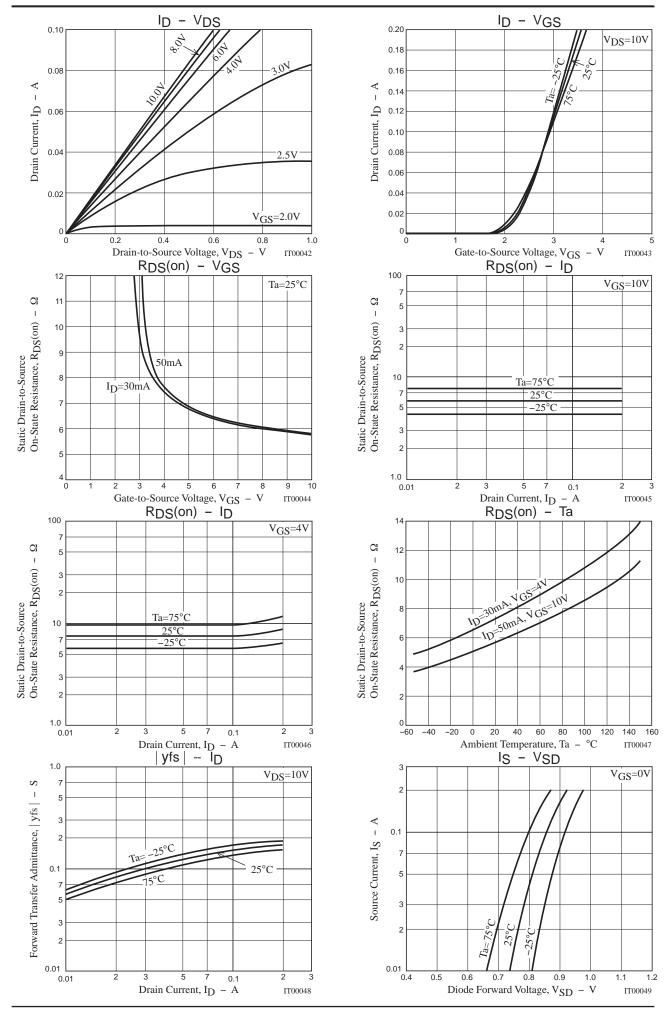
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Ullit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	50			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =50V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =100μA	1		2.4	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =50mA	85	120		mS	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =50mA, V _{GS} =10V		5.8	7.5	Ω	
	R _{DS} (on)2	ID=30mA, VGS=4V		7.5	10.5	Ω	
Input Capacitance	Ciss			6.2		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		4.4		pF	
Reverse Transfer Capacitance	Crss			1.5		pF	
Turn-ON Delay Time	t _d (on)			10		ns	
Rise Time	t _r	See appointed Test Circuit		11		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		105		ns	
Fall Time	tf			75		ns	
Total Gate Charge	Qg			1.40		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =100mA		0.21		nC	
Gate-to-Drain "Miller" Charge	Qgd			0.34		nC	
Diode Forward Voltage	VSD	IS=100mA, VGS=0V		0.85	1.2	V	

Switching Time Test Circuit

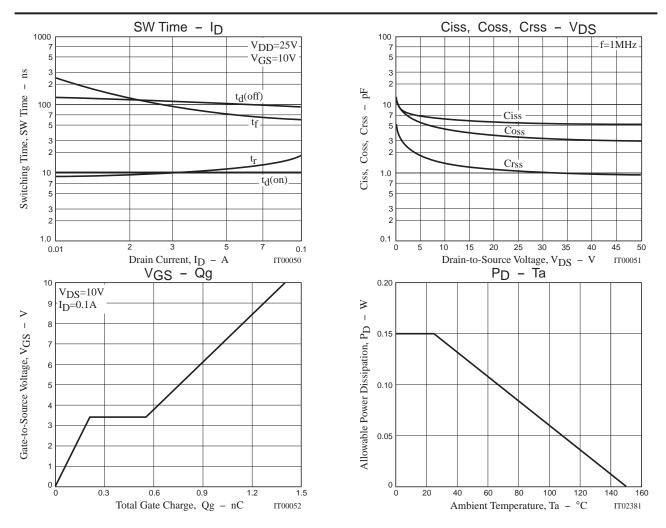


Ordering Information

Device	Package	Shipping	memo
5HN01M-TL-E	MCP	3,000pcs./reel	Pb Free
5HN01M-TL-H	MCP	3,000pcs./reel	Pb Free and Halogen Free



5HN01M

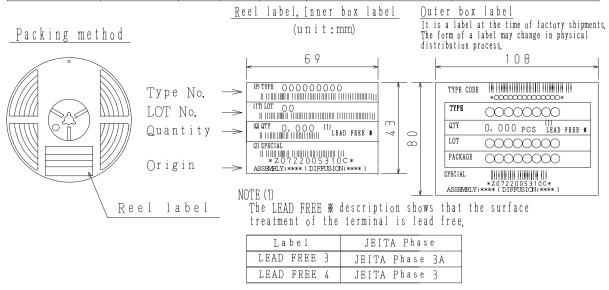


Embossed Taping Specification

5HN01M-TL-E, 5HN01M-TL-H

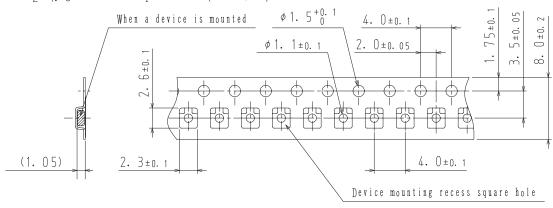
1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	g format	
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
MCP	MCP	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	

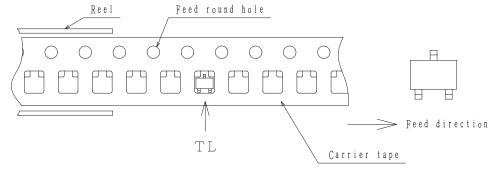


2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

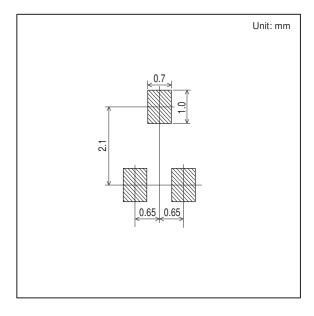


Those with oen electrode terminal on the feed hole side·····TL

Outline Drawing

5HN01M-TL-E, 5HN01M-TL-H

Land Pattern Example



Note on usage: Since the 5HN01M is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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